

## Description

The IRLML2502TRPBF uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

V<sub>DS</sub> = 20V I<sub>D</sub> =6 A

 $R_{DS(ON)} < 27m\Omega @ V_{GS}=4.5V$ 

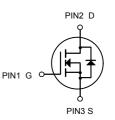
#### Application

Battery protection

Load switch Uninterruptible power supply







N-Channel MOSFET

#### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRLML2502TRPBF	SOT23	AE9T	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Symbol	Parameter		Limit	Unit	
VDS	Drain-Source Voltage		20	V	
Vgs	Gate-Source Voltage		±12	V	
Ι <sub>D</sub>	Continuous Drain Current	T <sub>A</sub> =25℃	6		
		T <sub>A</sub> =70℃	3.6	A	
Ідм	Drain Current-Pulsed (Note 1)		15	А	
PD	Maximum Power Dissipation		1.25	W	
TJ,TSTG	Operating Junction and Storage Temperature Range		-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)		100	°C <b>/W</b>	



# IRLML2502TRPBF

N-Channel Enhancement Mode MOSFET

## Electrical Characteristics (T<sub>A</sub>=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	20	22.5	-	V
Zero Gate Voltage Drain Current	ldss	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	$V_{DS}=V_{GS}$ , I <sub>D</sub> =250µA	0.5	0.65	1.0	V
	_	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.0 A	-	22	27	mΩ
Drain-Source On-State Resistance	Rds(on)	V <sub>GS</sub> =2.5V, I <sub>D</sub> =4.5A	-	28	40	mΩ
Forward Transconductance	gfs	V <sub>DS</sub> =10V,I <sub>D</sub> =4A	-	10	-	S
Input Capacitance	Clss		-	500	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =8V,V <sub>GS</sub> =0V,	-	295	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	96	-	PF
Turn-on Delay Time	td(on)		-	11	-	nS
Turn-on Rise Time	tr	VDD=10V.ID=1A	-	30	-	nS
Turn-Off Delay Time	td(off)	$V_{GS}$ =4.5V,R <sub>GEN</sub> =6 $\Omega$	-	35	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg		-	10	15	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =3A,V <sub>GS</sub> =4.5V	-	2.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	2.9	-	nC
Diode Forward Voltage (Note 3)	Vsd	V <sub>GS</sub> =0V,I <sub>S</sub> =1A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	4.5	Α

#### Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.

**2.** Surface mounted on FR4 Board, t  $\leq$  10 sec.

**3.** Pulse test: pulse width  $\leq$  300µs, duty cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**

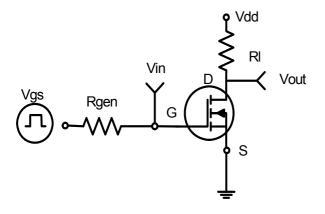


Figure 1:Switching Test Circuit

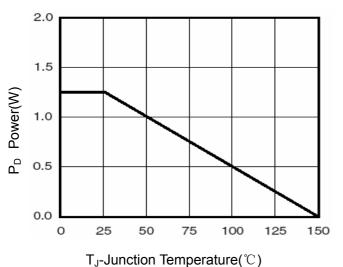
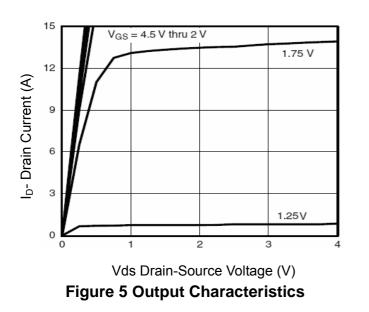


Figure 3 Power Dissipation



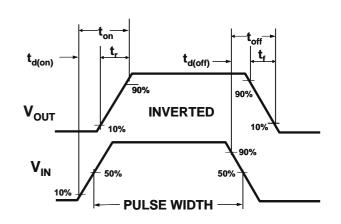
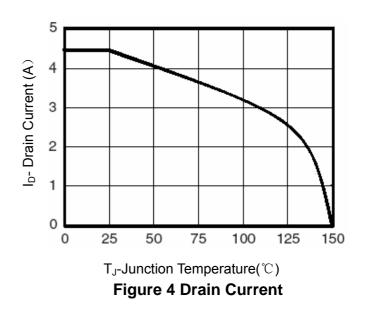
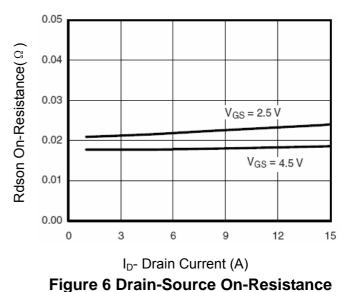


Figure 2:Switching Waveforms

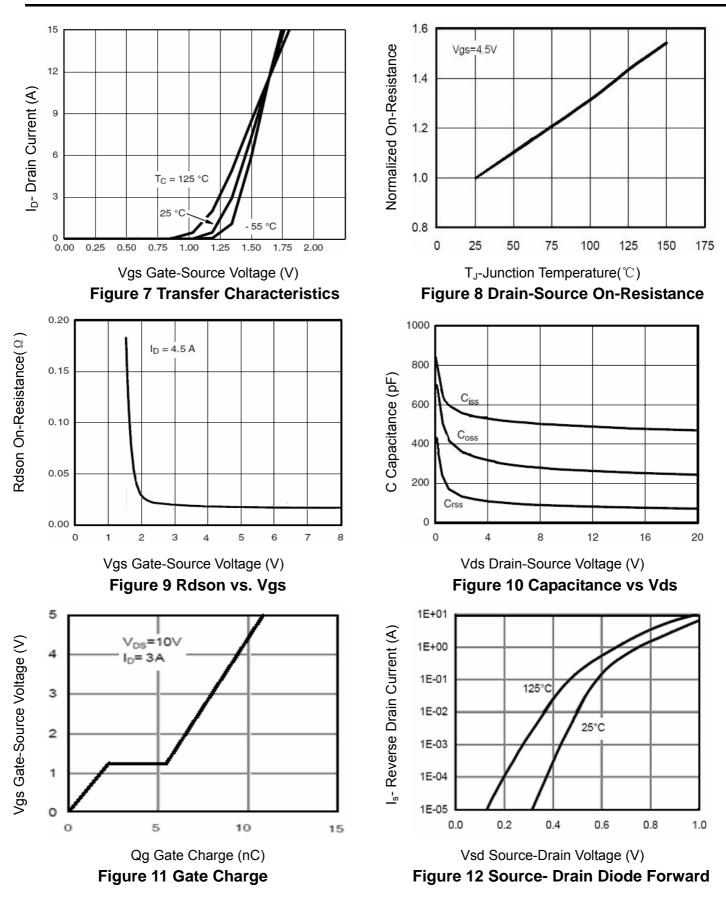


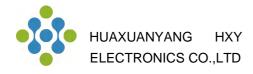




## IRLML2502TRPBF

N-Channel Enhancement Mode MOSFET





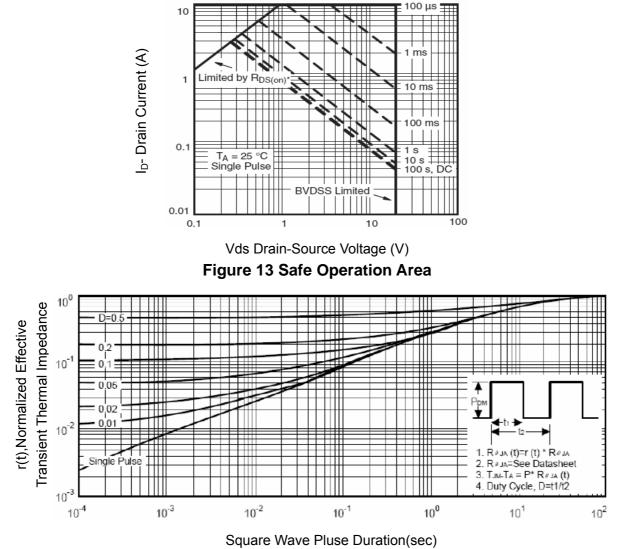
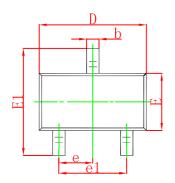
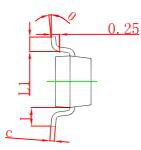


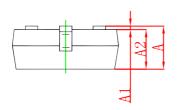
Figure 14 Normalized Maximum Transient Thermal Impedance



## **SOT-23 Package Outline Dimensions**

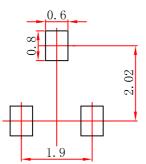






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
e	0.950	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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